

Theory of Bulk Recombination in a Medium with Energetic Disorder under Continuous Irradiation with Excitation Light

Kazuhiko Seki* and M. Tachiya†

National Institute of Advanced Industrial Science and Technology (AIST)

AIST Tsukuba Central 5, Higashi 1-1-1, Tsukuba, Ibaraki, Japan, 305-8565

Abstract

We study bulk recombination in a medium with energetic disorder under continuous irradiation with excitation light by using the multiple trapping (MT) model. Charge densities are shown to obey power law as a function of the intensity of excitation light, and the exponent is related to the dispersion parameter α of the MT model. The theory is applied to analyze charge densities in bulk heterojunction photovoltaic cells measured by light-induced electron spin resonance (LESR). The values of the exponent are consistent with those obtained from the transient decay of charge densities in time-resolved experiments. We show that the value of the exponent is robust against addition of Gaussian trapping energy distribution which is due to shallow trap states. In order to corroborate our theory, we also calculate the dependence of the open-circuit voltage on the light intensity on the basis of the same model and compare it with the corresponding experimental results.

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*Electronic address: k-seki@aist.go.jp

†Electronic address: m.tachiya@aist.go.jp

I. INTRODUCTION

In organic solar cells, it is important to suppress recombination between electrons and holes. So electron-hole recombination has been studied extensively in steady-state conditions in which the sample is continuously irradiated with an excitation light and in time-resolved conditions in which it is irradiated with a short pulse of the excitation light.

If recombination between electrons and holes occurs by an ordinary bimolecular reaction, the carrier density in the case when the sample is continuously irradiated with the excitation light should be proportional to $I^{0.5}$, where I is the light intensity. Recently Kuroda *et al.* ([1–3]) measured the dependence of the carrier density on the light intensity by using light-induced ESR (LESR). Although the observed data still have some scatter, they approximately followed a power law I^γ , but the power γ was much less than 0.5. Kuroda *et al.* explained this result by assuming that recombination occurred by a quadrimolecular reaction.

By the same token, if recombination between electrons and holes occurs by an ordinary bimolecular reaction, the decay of carriers after they are generated by a short pulse of the excitation light should be proportional to t^{-1} where t is the time after the pulse. Recently several groups ([4–7]) measured the decay kinetics of carriers. The observed data followed a power law $t^{-\beta}$ but β was much less than unity. This result was also explained by assuming that recombination occurred by multimolecular reaction with total reaction order larger than 2.

In the present paper, we explain the above two types of experimental results on the basis of the multiple trapping (MT) model. The MT model has been used in order to elucidate the kinetics of charge recombination processes. [8–13] The model used in the present paper was originally developed in 2002 in ref. [10]. In this paper the MT model which incorporates charge trap states with an exponential distribution of trapping energies was presented to analyze time-resolved kinetics of charge recombination in dye-sensitized solar cells and solved it analytically. In 2003 a similar model was used by Nelson to analyze time-resolved kinetics of charge recombination in organic solar cells. [9] However, in Nelson’s paper the model was not solved analytically but analyzed only by using numerical simulations. In 2009 we extended our model of 2002 to apply to time-resolved kinetics of charge recombination in organic solar cells,

and solved it analytically. [12] We showed theoretically on the basis of this theory that the total density of charges decays with time as $t^{-\beta}$ with β less than unity. In the MT model, charges perform transitions among trap states of different energies and the decelerated decay reflects the decrease in the detrapping rate as the distribution of charges among trap states of different energies shifts toward deeper trap levels inside the band gap. [10–12] A similar explanation was also given by other approaches. [14, 15]

If the total density of holes is changed in steady-state experiment by changing the light intensity, it changes distribution of holes among trap states with different trapping energies. This affects the open-circuit voltage (V_{OC}). In order to corroborate our theory, in the present paper we also calculate the dependence of the open-circuit voltage on the light intensity on the basis of our model and compare it with the corresponding experimental results.

In Sec. II, the MT model is generalized to apply to bulk recombination in the steady state conditions. V_{OC} is also calculated on the basis of the same model. Experimental results on steady-state and time-resolved conditions are analyzed in Sec. III. In Sec. IV, the results are compared to those obtained by other models. The last section is devoted to the conclusion.

II. THEORY

A. Charge recombination dynamics

Under the continuous irradiation with light, the excitons are generated. The electron-hole pairs are strongly bounded in excitons. The excitons can be dissociated into a hole and an electron at the interface between a donor phase and an acceptor phase in a bulk heterojunction. The charge generation rate, G , is proportional to the light intensity, I ,

$$G = k_g I. \quad (1)$$

The charges are initially produced in the free state. The motion of charges in bulk heterojunction solar cells has been described by the MT model. [16, 17] In the model, charges are trapped in the trap sites. We assume that if the detrapping rates of electrons and holes are different (This case is referred to as asymmetric case), carriers with the lower detrapping rate

are always trapped but those with the higher detrapping rate are partly trapped and partly free. For the sake of convenience we hereafter assume in the paper that holes have the higher detrapping rate. The results for the opposite case are easily obtained from those presented. The case when the detrapping rates of electrons and holes are identical (This case is referred to as symmetric case) is analyzed in Appendix B.

We assume that recombination between holes and electrons occurs once holes are detrapped. Therefore the recombination rate depends on the detrapping rates of holes. In time-resolved experiments distribution of holes among trap states with different trapping energies changes with time. This changes the detrapping rates of holes. We have shown theoretically in ref. [12] that the total density of holes decays with time as $t^{-\beta}$ with β less than unity instead of t^{-1} . In this paper we analyze steady-state experiments. If the total density of holes is changed in steady-state experiment by changing the light intensity, it changes distribution of holes among trap states with different trapping energies. This changes the detrapping rates of holes. We show theoretically that the total density of holes depends on the light intensity as I^γ with γ much less than 0.5 instead of $I^{0.5}$.

The trapping energy E of a hole is measured relative to the HOMO of the donor. We denote the trapping energy distribution by $g(E)$. We mainly treat the case when the trapping energy distribution is exponential. We also consider a more general case which includes an additional contribution of Gaussian trapping energy distribution. The detrapping rate constant is expressed as,

$$k_d(E) = \nu_d \exp(-E/k_B T), \quad (2)$$

where ν_d is the detrapping frequency. We use ν_d to normalize rates and introduce the dimensionless energy defined by $\epsilon = E/k_B T$. By thermal excitation, holes can be detrapped to the free state. The holes in the free state can either be trapped by vacant trap sites or recombine with trapped electrons.

Let $f(\epsilon)$ denotes the number density of holes trapped at trap sites with trapping energy ϵ .

In the steady state the distribution $f(\epsilon)$ obeys,

$$0 = G \frac{k_t [Ng(\epsilon) - f(\epsilon)]}{k_t(N - n) + k_r n} - e^{-\epsilon} f(\epsilon) + k_t \frac{Ng(\epsilon) - f(\epsilon)}{k_t(N - n) + k_r n} \int_0^\infty e^{-\epsilon} f(\epsilon) d\epsilon, \quad (3)$$

where the number density of trap sites is denoted by N . n is the total number density of holes and related to the number density of holes trapped with energy ϵ by,

$$n = \int_0^\infty f(\epsilon) d\epsilon. \quad (4)$$

The number density of electrons is the same as that of holes. k_t and k_r are the rate constants of a hole in the free state for trapping and for recombination with a trapped electron, respectively. G , k_t and k_r are normalized by ν_d as mentioned above. The first term on the right-hand side represents the generation rate of holes with trapping energy ϵ . The probability that a hole in the free state will be trapped in a trap state with trapping energy ϵ is proportional to k_t multiplied by the number density of the vacant trap sites given by $Ng(\epsilon) - f(\epsilon)$, where $Ng(\epsilon)$ is the total number density of trap states with trapping energy ϵ . The probability that a hole in the free state will recombine with a trapped electron is proportional to the recombination rate multiplied by the number density of electrons, n . Therefore, the probability that a hole in the free state will be trapped into a site with trapping energy ϵ can be written as,

$$\frac{k_t [Ng(\epsilon) - f(\epsilon)]}{k_t \int_0^\infty [Ng(\epsilon) - f(\epsilon)] d\epsilon + k_r n} = \frac{k_t [Ng(\epsilon) - f(\epsilon)]}{k_t N + (k_r - k_t) n}. \quad (5)$$

This factor is multiplied by a hole generation rate in the free state, G , to obtain the generation rate of holes with trapping energy ϵ . The second term on r.h.s. of Eq. (3) represents the decrease of holes with trapping energy ϵ by detrapping. The physical meaning of the third term on r.h.s. was previously explained in detail. [10–12]

By integrating Eq. (3) over ϵ , the fraction of trap sites occupied by holes, $\rho = n/N$, is shown to satisfy,

$$1 - \rho = y \int_0^\infty d\epsilon \exp(-\epsilon) f(\epsilon) / N, \quad (6)$$

where $\int_0^\infty g(\epsilon) d\epsilon = 1$ is used. y is given by

$$y = \frac{N k_r}{G k_t} \rho. \quad (7)$$

If the carrier generation rate G is high, y is small. In the steady state, the number density of holes trapped with trapping energy ϵ is obtained by introducing Eq. (6) in Eq. (3) as,

$$f(\epsilon) = \frac{N g(\epsilon)}{1 + y \exp(-\epsilon)}. \quad (8)$$

Equation (8) indicates that the number density of holes obeys a Fermi distribution as in equilibrium, and the quasi-Fermi energy of a hole relative to the HOMO of the donor can be defined by,

$$\epsilon_F = \ln(y). \quad (9)$$

Since y is given by Eq. (7), ϵ_F depends on the fraction of trap sites occupied by holes, $\rho = n/N$, and the light intensity through G . By substituting Eq. (7) into Eq. (9), we find that the quasi-Fermi energy depends logarithmically on ρ/G ,

$$\epsilon_F = \ln(k_r/k_t) + \ln(N\rho/G). \quad (10)$$

In the following, we derive the relation between ρ and G . The density of occupied sites is given by Eq. (8) regardless of the form of the trapping energy distribution. By substituting Eq. (8) in Eq. (4) and noticing $\rho = n/N$, we obtain,

$$\rho = \int_0^\infty d\epsilon \frac{g(\epsilon)}{1 + y \exp(-\epsilon)}. \quad (11)$$

By expanding the integrand in terms of y , Eq. (11) can be rewritten as,

$$\rho = \sum_{n=0}^{\infty} (-y)^n \hat{g}(n), \quad (12)$$

where $\hat{g}(n)$ denotes the Laplace transform of $g(\epsilon)$, $\hat{g}(n) = \int_0^\infty d\epsilon \exp(-n\epsilon) g(\epsilon)$. We note $\hat{g}(0) = 1$ from the normalization condition.

1. *Case of low carrier generation rate*

a. Exponential trapping energy distribution Here we assume that $g(E)$ decreases exponentially with increasing trapping energy,

$$g(E) = (1/E_0) \exp(-E/E_0), \quad (13)$$

where E_0 is a parameter indicating characteristic trapping energy. The trapping energy distribution can be expressed in the dimensionless unit as,

$$g(\epsilon) = \alpha \exp(-\alpha\epsilon). \quad (14)$$

$\alpha = k_B T/E_0$ is a key quantity in the MT model. α is called the dispersion parameter and given by the ratio of thermal energy to the characteristic trapping energy of trap sites. Small α compared with unity indicates that thermal energy is small compared with the typical trapping energy of trap states. Thermally assisted detrapping is suppressed when α is small.

We obtain $\hat{g}(n) = \alpha/(n + \alpha)$ for the exponential trapping energy distribution. By using this equation, Eq. (12) can be expressed as,

$$\rho = {}_2F_1(1, \alpha, 1 + \alpha, -y), \quad (15)$$

where ${}_2F_1(1, \alpha, 1 + \alpha, -y)$ is the hypergeometric function. [18]

If $y \gg 1$, Eq. (15) is simplified to the following equation by utilizing the asymptotic expansion of ${}_2F_1(1, \alpha, 1 + \alpha, -y)$,

$$\rho = \frac{\pi\alpha}{\sin(\pi\alpha)} y^{-\alpha}. \quad (16)$$

Equation (16) can be rewritten as a relation between the number density, ρ , and the charge generation rate, G ,

$$\rho \simeq \left(\frac{\pi\alpha}{\sin(\pi\alpha)} \right)^{1/(\alpha+1)} \left(\frac{Gk_t}{Nk_r} \right)^{\alpha/(\alpha+1)}. \quad (17)$$

Since the charge generation rate is proportional to the light intensity (Eq. (1)), the number density of holes obeys power law as a function of the light intensity and the exponent is given

by $\alpha/(\alpha+1)$. Equation (17) is valid under the condition $y \gg 1$. By using Eq. (7) we can show that this condition is equivalent to

$$\frac{\pi\alpha}{\sin(\pi\alpha)} \frac{k_r}{k_t} \frac{N}{G} \gg 1. \quad (18)$$

The power law dependence of ρ on the excitation light intensity, Eq. (17), is related to the transient decay kinetics of the total number density of holes. When the light irradiation is switched off, the hole density decays to its value under the dark condition. We have analyzed such a transient kinetics. For the exponential trapping energy distribution, the transient time dependence of the hole density is derived as, [12]

$$\rho(t) \sim 1/t^\alpha, \quad (19)$$

where α is again the dispersion parameter. The value of α in Eq. (19) should be equal to that in Eq. (17).

b. Influence of shallow trap states We now consider a more general case which includes an additional contribution of Gaussian distribution in the trapping energy distribution,

$$g(\epsilon) = p\alpha \exp(-\alpha\epsilon) + (1-p) \frac{1}{\sqrt{2\pi\sigma^2}c_N} \exp\left(-\frac{(\epsilon - \epsilon_m)^2}{2\sigma^2}\right), \quad (20)$$

where p denotes the fraction of sites represented by the exponential trapping energy distribution. c_N is introduced to normalize the truncated Gaussian distribution in which ϵ takes only positive values. It is given by, $c_N = (2\pi\sigma^2)^{-1/2} \int_0^\infty d\epsilon \exp[-(\epsilon - \epsilon_m)^2/(2\sigma^2)]$. The density of states given by the sum of Gaussian and exponential distributions were successfully used to describe hole densities in blend films of RR-P3HT and PCBM. [19] If we substitute Eq. (8) together with Eq. (20) instead of Eq. (13) in Eq. (6), Eq. (16) is generalized to,

$$\rho = p \frac{\pi\alpha}{\sin \pi\alpha} \frac{1}{y^\alpha} + (1-p) \frac{\exp(\epsilon_m)}{y + \exp(-\epsilon_m)} \quad (21)$$

$$\approx p \frac{\pi\alpha}{\sin \pi\alpha} \frac{1}{y^\alpha} + (1-p) \exp(\epsilon_m) / y. \quad (22)$$

In the derivation we used the following approximation,

$$\int_0^\infty d\epsilon g(\epsilon) \frac{1}{1 + y^{-1} \exp(\epsilon)} \approx \frac{y}{y + \exp(\epsilon_m)}, \quad (23)$$

and extended the lower limit of integration to $-\infty$ by assuming $0 \ll \sigma \ll \epsilon_m$ and retained just the leading term by expanding $1/[1 + y^{-1} \exp(\epsilon)]$ about $\epsilon = \epsilon_m$. We further took the asymptotic limit, $y \gg \exp(\epsilon_m)$. By substituting Eq. (7) into Eq. (22) we obtain,

$$\rho = p \frac{\pi \alpha}{\sin \pi \alpha} \left(\frac{k_t}{k_r} \frac{G}{N} \frac{1}{\rho} \right)^\alpha + (1 - p) \exp(\epsilon_m) \frac{k_t}{k_r} \frac{G}{N} \frac{1}{\rho}. \quad (24)$$

When $p(\pi \alpha)/(\sin \pi \alpha) \geq (1 - p) \exp(\epsilon_m)$ and/or in the limit of weak light intensity, Eq. (24) leads to the same power law as that given by Eq. (17). As long as the tail of trap states can be approximated by an exponential trapping energy distribution (Eq. (14)), the exponent for the power law dependence of the hole density on the continuous light intensity is robust and is given by $\alpha/(1 + \alpha)$ even in the presence of additional shallow states.

In the ordinary theory of bimolecular recombination in the absence of trap states, the hole density as a function of continuous light intensity is given by power law with the exponent 0.5. The same result is obtained when we consider Gaussian trapping energy distribution,

$$g(\epsilon) = \frac{1}{\sqrt{2\pi\sigma^2} c_N} \exp\left(-\frac{(\epsilon - \epsilon_m)^2}{2\sigma^2}\right), \quad (25)$$

with a small width of energy distribution, $\sigma \ll \epsilon_m$. By setting $p = 0$ in Eq. (24) we get

$$\rho = \exp(\epsilon_m/2) \sqrt{\frac{k_t}{k_r} \frac{G}{N}}, \quad (26)$$

as expected. Note that Eq. (26) is obtained by assuming $y \gg \exp(\epsilon_m) \gg 1$.

2. Case of high carrier generation rate

If $y \ll 1$, we obtain the following equation by retaining the first two terms in Eq. (12) and further using Eq. (7),

$$\rho \simeq \left(1 + \frac{k_r \hat{g}(1) N}{k_t G} \right)^{-1}. \quad (27)$$

The fraction ρ of trap sites occupied by carriers saturates when the light intensity is high. The saturation results from the filling of the trap levels inside the band gap up to the shallow trap levels. Note that Eq. (27) is derived without assuming any form of the trapping energy distribution.

B. Open-circuit voltage

According to the MT model, distribution of holes among trap states with different trapping energies can be characterized by the quasi-Fermi energy. Figure 1 shows the hole density as a function of the trapping energy for the exponential (A) and Gaussian (B) trapping energy distributions. In both (A) and (B), the hole density is shown for two light intensities which are different by a factor of 10. Suppose that the quasi-Fermi energy at the low light intensity is the same for both (A) and (B). The thick dashed line in (A) and (B) indicates the quasi-Fermi energy when the light intensity is increased 10 times. For this change of the light intensity the quasi-Fermi energy for the exponential trapping energy distribution decreases more than that for the Gaussian trapping energy distribution. In other words, the amount of change in the quasi-Fermi energy by increasing light intensity depends on the form of $g(\epsilon)$. It implies that the open-circuit voltage estimated from the quasi-Fermi energy is affected by the trapping energy distribution and the light intensity; the open-circuit voltage in the case of the exponential trapping energy distribution depends on the light intensity more strongly compared to that in the case of the Gaussian trapping energy distribution.

We now study quantitatively the influence of the trapping energy distribution on the open-circuit voltage under the illumination of continuous light. In open-circuit condition, the current is not extracted and the photogenerated carriers in principle disappear only by recombination. When recombination is in equilibrium with generation of charge pairs, the open-circuit voltage is given by the difference between the quasi-Fermi energy of a hole and that of an electron both measured from the same level, for example, the HOMO level of the donor, [20, 21]

$$eV_{\text{OC}} = (k_B T) \left(\epsilon_F^{(e)} - \epsilon_F \right), \quad (28)$$

where $\epsilon_F^{(e)}$ is the quasi-Fermi level of an electron measured from the HOMO level of the donor.

We first consider an asymmetric case and assume that the detrapping frequency of electrons, $\nu_d^{(e)}$, is smaller than that of holes, ν_d , $\xi = \nu_d^{(e)} / \nu_d \ll 1$. When $\xi = \nu_d^{(e)} / \nu_d \ll 1$, the quasi-Fermi energy of a hole can be approximated by Eq. (10). In Appendix A, the quasi-Fermi energy of an electron in this case is calculated as Eq. (A.6). This quasi-Fermi energy of an electron, $\epsilon_F'^{(e)}$, is measured from the LUMO level of the acceptor in the downward direction. (See Fig. 2

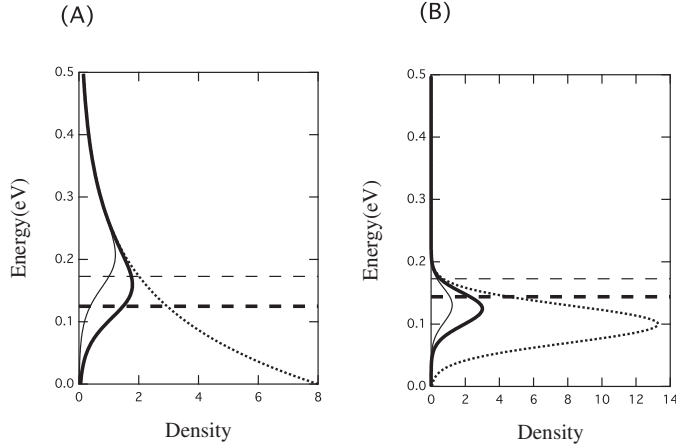


FIG. 1: (A) Hole density as a function of the trapping energy for the exponential trapping energy distribution with $\alpha = 0.2$. Dotted line represents the exponential trapping energy distribution of trap states given by Eq. (14). The thin solid line represents the distribution given by $f(\epsilon)/N$ with the quasi-Fermi energy equal to 0.173 [eV] which is indicated by the thin dashed line. The thick solid line shows the distribution when the light intensity is increased 10 times. The quasi-Fermi energy for this case is equal to 0.125 [eV] and is indicated by the thick dashed line. (B) Hole density as a function of the trapping energy for the Gaussian trapping energy distribution with the mean and the variance given by 0.1 [eV] and 0.03 [eV], respectively. Dotted line represents the Gaussian trapping energy distribution of trap states given by Eq. (25). The thin solid line represents the distribution given by $f(\epsilon)/N$ with the quasi-Fermi energy equal to 0.173 [eV] which is indicated by the thin dashed line. The thick solid line shows the distribution when the light intensity is increased 10 times. The quasi-Fermi energy for this case is equal to 0.144 [eV] and is indicated by the thick dashed line.

for the energy coordinates.) The quasi-Fermi energy of an electron measured from the HOMO level of the donor in the upward direction is given by,

$$\epsilon_F^{(e)} = \text{acceptor LUMO level} - \text{donor HOMO level} - \epsilon_F^{\prime(e)} \quad (29)$$

$$= \text{acceptor LUMO level} - \text{donor HOMO level} - \log(\xi k_t/k_r) - \epsilon_F, \quad (30)$$

where $\epsilon_F^{\prime(e)}$ given by Eq. (A.6) is substituted. We treat the two cases when the trapping energy distribution of holes is Gaussian and when the trapping energy distribution of holes is

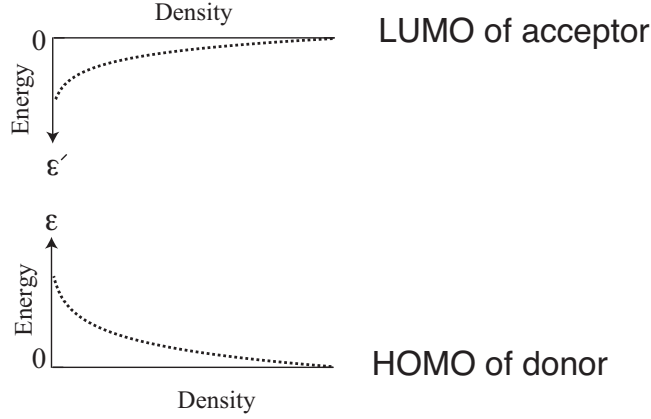


FIG. 2: Schematic representation of ϵ and ϵ' coordinates of trap states.

exponential.

1. *Case of low carrier generation rate*

a. Gaussian trapping energy distribution When the trapping energy distribution is Gaussian, the quasi-Fermi energy of a hole measured from the HOMO level of the donor is obtained by substituting Eq. (26) in Eq. (10),

$$\epsilon_F = (1/2) [\epsilon_m + \ln(k_r/k_t) - \ln(G/N)]. \quad (31)$$

By substituting Eqs. (30) and (31) in Eq. (28), V_{OC} is obtained as a linear function of the logarithm of light intensity, I ,

$$V_{OC} = c_1 + (k_B T/e) \ln I, \quad (32)$$

where Eq. (1) was used and c_1 is a constant independent of the light intensity. According to Eq. (32), the relation between V_{OC} and $\ln I$ is linear with a positive slope equal to $k_B T/e$. This is indeed observed experimentally. [22, 23] Equation (32) was also derived by assuming a single trap state both for a hole and an electron. [22–24]

b. Exponential trapping energy distribution When the trapping energy distribution is exponential, the quasi-Fermi energy of a hole is obtained by substituting Eq. (17) in Eq. (10),

$$\epsilon_F = \frac{1}{\alpha + 1} \left[\ln \left(\frac{\pi\alpha}{\sin \pi\alpha} \right) + \ln(k_r/k_t) - \ln(G/N) \right]. \quad (33)$$

By substituting Eqs. (30) and (33) in Eq. (28) V_{OC} is obtained as,

$$V_{OC} = c_2 + [2/(\alpha + 1)] (k_B T/e) \ln I, \quad (34)$$

where c_2 is a constant independent of the light intensity. The slope of V_{OC} against $\ln I$ could be in the range between $k_B T/e$ and $2k_B T/e$ in this case. As already mentioned, Eq. (17) is valid for $[\pi\alpha/\sin(\pi\alpha)](k_r/k_t)(N/G) \gg 1$. Therefore, Eq. (34) is also valid under this condition. The slope larger than $k_B T/e$ is recently reported in bulk heterojunction solar cells, where charge transport is trap-limited. [22, 25, 26]

So far, we have assumed that the hopping frequency of holes is larger than that of electrons. In the opposite situation, α in Eq. (34) should be replaced by that for electrons.

2. Case of high carrier generation rate

By using Eq. (7) we can show that the condition of $y \ll 1$ is equivalent to

$$\frac{\pi\alpha}{\sin(\pi\alpha)} \frac{k_r}{k_t} \frac{N}{G} \ll 1. \quad (35)$$

By using Eq. (27), Eq. (7) can be expressed as,

$$\begin{aligned} y &\simeq \left[\hat{g}(1) + \frac{k_t}{k_r} \frac{G}{N} \right]^{-1} \\ &\simeq \frac{k_r}{k_t} \frac{N}{G}, \end{aligned} \quad (36)$$

where Eq. (35) and $\hat{g}(1) < 1$ are used. As a result, $\epsilon_F = \ln y$ is obtained as,

$$\epsilon_F \simeq \ln(k_r/k_t) - \ln(G/N). \quad (37)$$

By substituting Eqs. (30) and (37) in Eq. (28), V_{OC} is obtained as a linear function of the logarithm of light intensity, I ,

$$V_{OC} = c_1 + 2(k_B T/e) \ln I. \quad (38)$$

It should be reminded that when the light intensity is high, this relation is derived without assuming any specific forms of $g(\epsilon)$. The slope of V_{OC} vs $\ln(I)$ is given by $2k_B T/e$ regardless of the forms of $g(\epsilon)$ as a result of trap filling effect explained below.

3. Case of identical kinetic parameters of electrons and holes

Recently, the relations given by Eq. (32) and Eq. (34) have also been found by numerical simulations when the kinetic parameters of electrons and holes are identical. [27] Equation (32) is found for the Gaussian trapping energy distribution and Eq. (34) is found for the exponential trapping energy distribution. [27] In the simulation, the drift-diffusion equation was solved together with the Poisson's equation, and the carrier density in the trap states, ρ_t , was approximated as $\rho_t \sim \exp(-E'_f/E_0)$ in terms of the quasi-electrochemical potential E'_f determined self-consistently. The results were interpreted by using ρ_t given above with spatially homogeneous E'_f . [27, 28]

Here, we calculate V_{OC} analytically in the case when the kinetic parameters of electrons and holes are identical. If y given by Eq. (B.4) is larger than unity, the quasi-Fermi energy is given by Eq. (B.8). Since we have $\epsilon_F^{(e)} = \epsilon_F$, V_{OC} is obtained as Eq. (34) by using Eq. (B.8) and Eqs. (28)-(29). Equation (34) is valid when y given by Eq. (B.4) is larger than unity which is equivalent to

$$\frac{2k_t k_r}{(k_t + k_r)^2} \frac{N}{G} \gg 1. \quad (39)$$

Let us consider the opposite limit $y \ll 1$ which is equivalent to,

$$\frac{2k_t k_r}{(k_t + k_r)^2} \frac{N}{G} \ll 1. \quad (40)$$

This condition is satisfied under the strong light intensity leading to high carrier generation rate, G . The quasi-Fermi energy is given by Eq. (B.11). Since we have $\epsilon_F^{(e)} = \epsilon_F$, V_{OC} is obtained as Eq. (38) by using Eq. (B.11) and Eqs. (28)-(29).

III. ANALYSIS OF EXPERIMENTAL RESULTS

A. Dependence of stationary hole density on excitation light intensity

Charge carrier density in the composite of regioregular poly3-hexylthiophene (RR-P3HT) and 6,6-phenyl-C61-butyric acid methyl ester (PCBM) was recently measured by LESR under the continuous irradiation with light. [1] LESR technique has been applied to probe the holes on the polymer and fullerene radical anions. [1–3]

In Fig. 3, the hole density measured by LESR is shown against excitation light intensity for different PCBM concentrations. [1] We analyzed these results by using power law dependence on the excitation light intensity. As shown in Fig. 3, the values of α estimated by using Eq. (17) are within the range of 0.26–0.35. These values can be assessed by analyzing the transient kinetics.

B. Time-resolved decay of hole density

As shown in Fig. 4, the decay of the hole density in time-resolved experiments obeys power law and we obtained α as 0.3 for 5 mol % of PCBM by using Eq. (19). This value is consistent with $\alpha = 0.31$ estimated from Fig. 3 by using Eq. (17). The difference between the fit with $\alpha = 0.31$ and the best fit with $\alpha = 0.3$ is small as shown in Fig. 4. The results indicate the applicability of MT model to interpret the experimental data on both the steady state and time-resolved conditions. Unfortunately, the experimental results shown in Fig. 3 are not sufficiently accurate. More accurate and systematic measurements of experimental data are badly needed in order to make a more quantitative comparison between our theory and experiment.

Now we analyze the temperature dependence of the decay kinetics. Unfortunately, detailed data on the temperature dependence of the decay kinetics are not available for this sample. So, we analyze the temperature dependence of the decay kinetics for other samples.

Figure 5 (A) shows the decay of the hole density for RR-poly(3-octylthiophene)(P3OT)/fullerene at temperatures, 60, 80, and 100 K. [3] All results

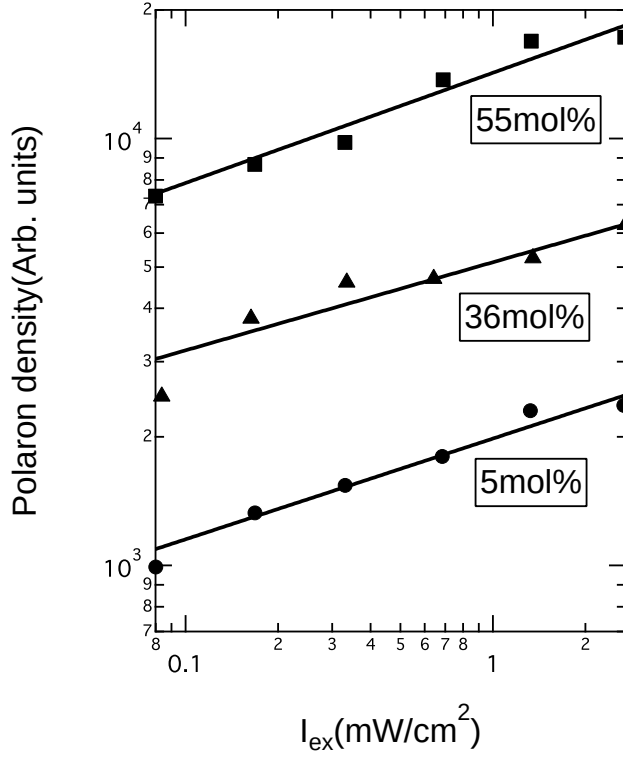


FIG. 3: Hole density against excitation light intensity of 670 nm. RR-P3HT/PCBM for different PCBM concentrations measured at 60 K. [1] The lines indicate the fitting by Eq. (17). α values extracted from the fitting are $\alpha = 0.35$ for 55 mol %, $\alpha = 0.26$ for 36 mol % and $\alpha = 0.31$ for 5 mol %. For 5 mol % the value of the exponent is $\alpha/(\alpha + 1) = 0.236$.

indicate power law decay at long times. The value of the exponent α obtained from the decay kinetics is shown in Fig. 5 (B) as a function of temperature. α can be well approximated by a linear function of temperature and is almost proportional to temperature. This is consistent with the MT model which incorporates an exponential trapping energy distribution. It predicts $\alpha = k_B T / E_0$. Power law decay of the hole density and linear temperature dependence of α is also found for RR-P3HT/fullerene as shown in Fig. 6. The dispersion parameter α should be proportional to the temperature if the trapping energy distribution is strictly exponential. The deviation indicates that the trapping energy distribution is not strictly exponential.

In Figs. 5 and 6 the same acceptor was used, but the length of alkyl chains was changed.

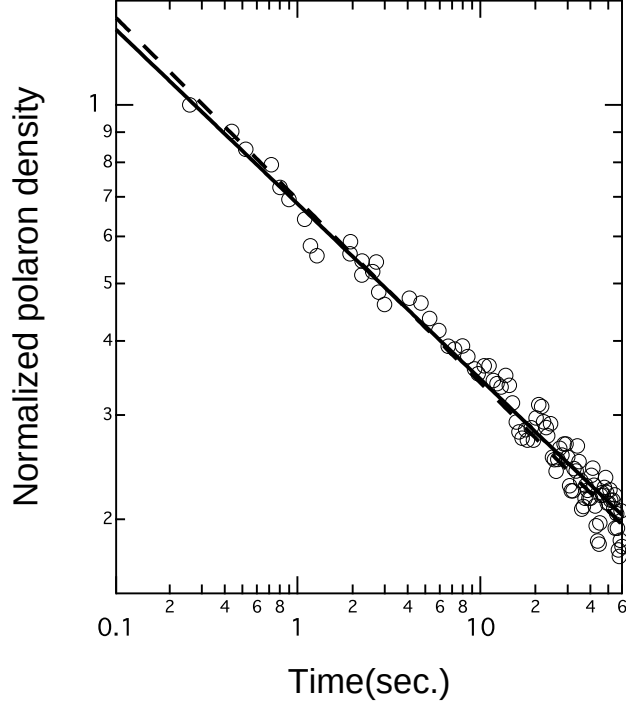


FIG. 4: Normalized hole density against time after the switch-off of the excitation light of 670 nm with 2.7 mW/cm^2 . RR-P3HT/PCBM with 5 mol % PCBM measured at 60 K. [1] The solid line indicates the best fit by power law kinetics with $\alpha = 0.3$. The dashed line shows the fitting with $\alpha = 0.31$ obtained by analyzing Fig. 3.

If experimental data are more accurate and systematic, more information will be obtained on the effect of alkyl chain length on the trapping energy distribution by comparing Figs. 5 and 6. More accurate and systematic measurements of experimental data are badly needed in order to make a more quantitative comparison between our theory and experiment.

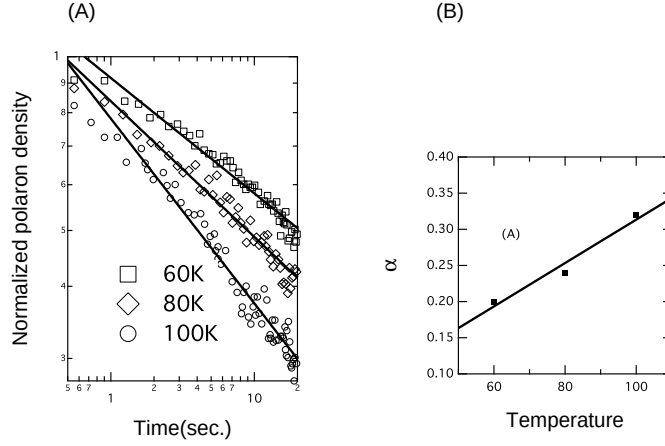


FIG. 5: (A) Normalized hole density against time. RR-P3OT/fullerene with 5 mol % fullerene measured at 60, 80, and 100 K. [3] The excitation light of 700 nm with 1 mW/cm² is switched off at time zero. Squares, diamonds, and circles correspond to 60K, 80K, and 100K, respectively. The solid lines are the fits by power law kinetics, Eq. (19). (B) α values determined by fitting to Eq. (19) as a function of temperature. The line represents the result of fitting by $\alpha = 0.01 + T/333$.

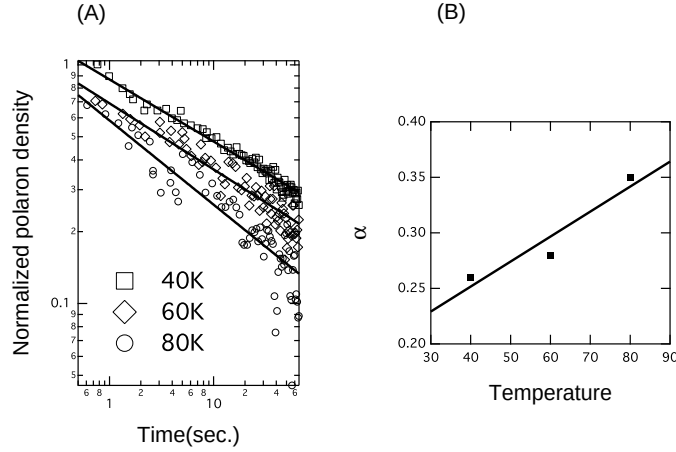


FIG. 6: (A) Normalized hole density against time. RR-P3HT/fullerene with 5 mol % fullerene measured at 40, 60, and 80 K. [2] The excitation light of 700 nm with 0.25 mW/cm² is switched off at time zero. Squares, diamonds, and circles correspond to 40K, 60K, and 80K, respectively. The solid lines are the fits by power law kinetics, Eq. (19). (B) α values determined by fitting to Eq. (19) as a function of temperature. The line represents the result of fitting by $\alpha = 0.162 + T/444$.

IV. DISCUSSION

We have assumed that recombination between holes and electrons occurs once holes are detrapped. Therefore the recombination rate depends on the detrapping rates of holes. In time-resolved experiments distribution of holes among trap states with different trapping energies changes with time. This changes the detrapping rates of holes. We have shown theoretically that the total density of holes decays with time as $t^{-\beta}$ with β less than unity instead of t^{-1} . If the total density of holes is changed in steady-state experiment by changing the light intensity, it changes distribution of holes among trap states with different trapping energies. This changes the detrapping rates of holes. We have shown theoretically that the total density of holes depends on the light intensity as I^γ with γ much less than 0.5 instead of $I^{0.5}$.

In the multimolecular reaction model the recombination between electrons and holes is assumed to occur by multimolecular reaction between electrons and holes. When total reaction order is m , the recombination rate is proportional to the m th power of the total density of holes, if the total densities of holes and electrons are equal. In the multimolecular reaction model the recombination rate is assumed to be proportional to the densities of holes and electrons and the rate coefficient is implicitly assumed to be a constant. If this assumption is made, in steady-state experiments the total density of holes depends on the light intensity as $I^{1/m}$. However, it should be pointed out that the rate coefficient in this case is not a constant for the following reason. If the density of holes is changed in steady-state experiments by changing the light intensity, it changes the distribution of holes among trap states with different trapping energies. This changes detrapping rates of holes and therefore changes recombination rates with electrons. In our opinion this is the reason the reaction order larger than 2 is obtained, if experiments are analyzed on the basis of the multimolecular reaction model. The same criticism also applies to the analysis of time-resolved experiments on the basis of the multimolecular reaction model.

Previously, the trap-limited recombination has been interpreted by using the Shockley-Read-Hall(SRH) theory. [29] The original SRH theory of recombination assumes a single trap state in a material composed of a single phase. The original SRH model can be extended to the case

of trap states with an exponential distribution of trapping energies. [28] However, it should be pointed out that since the original SRH theory assumes the steady state, it cannot be applied to analyze transient kinetics.

There is another important assumption in the SRH model. It assumes that a trap state, say, for an electron, can trap an electron efficiently, if it is empty, not only from the conduction band but also from the valence band. In our opinion, this assumption is reasonable for inorganic semiconductors but not for organic semiconductors. In organic semiconductors the electron trapping energy distribution does not extend very deep inside the band gap from the conduction band edge. In other words, trap states are located close to the conduction band edge but far away from the valence band edge. As a result, a trap state can trap an electron efficiently from the conduction band but not efficiently from the valence band. In our model we assume that trapping and detrapping of a hole from/to the valence band occur efficiently and recombination occurs efficiently between free holes and trapped electrons.

There are several differences between our theory and those in refs [27] and [28]. Differences are as follows.

In our model the kinetic parameters of holes and electrons are in general different, while in their models it is assumed that electrons and holes have identical kinetic parameters.

In our model the spatial variation of electrostatic potential is not taken into account, while in their models it is taken into account. When the spatial variation of the carrier density is small, their results agree with ours.

Our model is solved analytically, while their models are analyzed mainly by using numerical simulations. In our theory the carrier distribution among the trap states are calculated rigorously, while in their models it is calculated only approximately. In this paper, we have solved the symmetric case as well analytically to compare with their corresponding results obtained numerically and with our results on the asymmetric case.

In their models, the direct recombination between free holes and free electrons was also taken into account. [27, 28] It was shown that the open circuit voltage can be limited by direct recombination when the trapping rates of free carriers are very small. [28] Direct recombination between trapped holes and trapped electrons was also taken into account in a simulation, though

recombination between free carriers and trapped carriers of opposite charge was considered to be dominant. [27] In this paper we assume that recombination occurs between free holes and trapped electrons. We assume that holes are mostly in trap states and can recombine with trapped electrons once they are detrapped to the conduction band and become free. We do not think that in organic semiconductors holes trapped near the valence band edge recombine efficiently with electrons trapped near the conduction band edge.

It should also be pointed out that when they derived Eq. (34) for the exponential trapping energy distribution, they implicitly assumed that the light intensity is low, so that the generation rate is also low. In this case the condition given by Eq. (39) holds and V_{OC} is obtained as Eq. (34). However, in the opposite limit given by Eq. (40) we have shown that V_{OC} is obtained as Eq. (38) as already shown.

The above results are explained on the basis of the trap filling effect. Trap states have different trapping energies. When the light intensity is low, only deep trap levels inside the band gap are occupied by charges. When the light intensity is high, shallow trap levels close to the conduction band are also occupied. Charges occupied in shallow trap states are easily detrapped to the conduction band, so they behave like quasifree charges. Accordingly the slope of V_{OC} vs $\ln I$ becomes independent of the form of $g(\epsilon)$. The trap filling effect is important when the light intensity is high and the number of trap states is small. On the other hand, the condition given by Eq. (39) holds when the light intensity is low and the number of trap sites is large. In this paper we calculate V_{OC} in both limits of (a) low light intensity with large trap site number and (b) high light intensity with small trap site number.

V. CONCLUSION

In this paper, we have analyzed recently observed power law dependence of the charge density on the intensity of excitation light by using the MT model. The observed relation between the hole density n and the excitation light I obeys power law, $n \sim I^\gamma$, where γ is smaller than 0.5. Previously, the exponent γ smaller than 0.5 was explained by assuming quadrimolecular recombination among holes and electrons. By using the MT model, we have

successfully explained the experimental results of $\gamma < 0.5$. To be more precise, the exponent is given in terms of the dispersion parameter α as $\gamma = \alpha/(1 + \alpha)$ and α should be smaller than 1 when the deep trap levels inside the band gap is described by an exponential trapping energy distribution.

The value of the exponent is consistent with that obtained from the independent experiment on the transient decay of charge density. Analysis of the temperature dependence of the exponent obtained from the transient decay shows that the temperature dependence of the exponent is consistent with the MT model. The value of the exponent is robust against addition of Gaussian trapping energy distribution to the usual exponential trapping energy distribution, the former representing shallow trap states and the latter representing deep trap states. Even under the presence of shallow trap states the exponent characterizes the exponential trapping energy distribution of deep trap states.

We also show that V_{OC} depends linearly on the logarithm of light intensity and the slope is equal to $k_B T/e$ when only the shallow trap states are present. Otherwise, the same linear relation holds but the slope is larger than $k_B T/e$.

Appendix A. The detrapping rates of electrons and holes are different (Asymmetric case)

We consider the case when the detrapping frequency of electrons is smaller than that of holes, namely $\xi = \nu_d^{(e)}/\nu_d \ll 1$. Let $f_e(\epsilon')$ denote the number density of electrons trapped at trap sites with the trapping energy ϵ' . The trapping energy ϵ' of an electron is measured relative to the LUMO of the acceptor. In the steady state, $f_e(\epsilon')$ obeys the equation similar to Eq. (3),

$$\begin{aligned} 0 = & G \frac{k_t^{(e)} [N_e g_e(\epsilon') - f_e(\epsilon')]}{k_t^{(e)} (N_e - n) + k_r^{(e)} n} - G \frac{k_r f_e(\epsilon')}{k_t (N - n) + k_r n} \\ & - \xi e^{-\epsilon'} f_e(\epsilon') + k_t^{(e)} \frac{N_e g_e(\epsilon') - f_e(\epsilon')}{k_t^{(e)} (N_e - n) + k_r^{(e)} n} \xi \\ & \times \int_0^\infty e^{-\epsilon'} f_e(\epsilon') d\epsilon' - k_r \frac{f_e(\epsilon')}{k_t (N - n) + k_r n} \int_0^\infty e^{-\epsilon} f(\epsilon) d\epsilon, \end{aligned} \quad (\text{A.1})$$

where the number density of trap sites for electrons is denoted by N_e , the second term on the right-hand side represents loss of trapped electrons with trapping energy ϵ' due to recombination with generated holes, and the last term represents loss of trapped electrons with trapping energy ϵ' due to recombination with holes detrapped into the free state.

When $\xi \int_0^\infty e^{-\epsilon'} f_e(\epsilon') d\epsilon' \ll \int_0^\infty e^{-\epsilon} f(\epsilon) d\epsilon$, $k_r^{(e)} \ll k_t^{(e)}$, and $k_r \ll k_t$, Eq. (A.1) simplifies into,

$$G g_e(\epsilon') = \xi e^{-\epsilon'} f_e(\epsilon') + \frac{G}{N_e} f_e(\epsilon') + f_e(\epsilon') \frac{k_r}{k_t} \frac{1}{N} \int_0^\infty e^{-\epsilon} f(\epsilon) d\epsilon. \quad (\text{A.2})$$

If the fraction of trap sites occupied by holes is small, Eq. (6) can be rewritten as,

$$\int_0^\infty d\epsilon e^{-\epsilon} f(\epsilon) = \frac{k_t}{k_r} \frac{G}{\rho}. \quad (\text{A.3})$$

By substituting Eq. (A.3) into Eq. (A.2), we obtain,

$$f_e(\epsilon') = \frac{N \rho g_e(\epsilon')}{G} \frac{1}{1 + y_e \exp(-\epsilon')}, \quad (\text{A.4})$$

when $\rho \ll N_e/N$, where y_e is given by,

$$y_e = \frac{N}{G} \rho \xi. \quad (\text{A.5})$$

y_e can be further rewritten as $y_e = \xi(k_t/k_r)y$ in terms of y defined by Eq. (7). Therefore, the quasi-Fermi energy of an electron relative to the LUMO of the acceptor is given by,

$$\epsilon_F'^{(e)} = \log y_e = \log(\xi k_t/k_r) + \epsilon_F. \quad (\text{A.6})$$

Appendix B. The detrapping rates of electrons and holes are identical (Symmetric case)

We first note that Eq. (A.1) holds without any restriction on the kinetic parameters of electrons and holes. If the kinetic parameters of electrons and holes are identical, Eq. (A.1) can be simplified as,

$$0 = G \frac{k_t [Ng(\epsilon) - f(\epsilon)] - k_r f(\epsilon)}{k_t(N - n) + k_r n} - e^{-\epsilon} f(\epsilon) + \frac{k_t [Ng(\epsilon) - f(\epsilon)] - k_r f(\epsilon)}{k_t(N - n) + k_r n} \int_0^\infty e^{-\epsilon} f(\epsilon) d\epsilon. \quad (\text{B.1})$$

By integrating Eq. (B.1) over ϵ , we obtain,

$$G = \frac{2k_r n (G + \int_0^\infty e^{-\epsilon} f(\epsilon) d\epsilon)}{k_t(N - n) + k_r n}. \quad (\text{B.2})$$

Equation (B.1) can be rewritten by using Eq. (B.2) as

$$f(\epsilon) = \left(\frac{k_t}{k_t + k_r} \right) \frac{Ng(\epsilon)}{1 + y \exp(-\epsilon)}, \quad (\text{B.3})$$

where y is given by,

$$y = \frac{N}{G} \frac{2k_r}{k_t + k_r} \rho. \quad (\text{B.4})$$

It is interesting to note that if we introduce ϵ_F through $y = \exp(\epsilon_F)$, Eq. (B.3) represents the Fermi-Dirac distribution with the quasi-Fermi energy given by ϵ_F . By introducing Eq. (B.3) into Eq. (4), we obtain,

$$\rho = \frac{k_t}{k_t + k_r} \int_0^\infty d\epsilon \frac{g(\epsilon)}{1 + y \exp(-\epsilon)}. \quad (\text{B.5})$$

Equation (B.5) is expressed as,

$$\rho = \frac{k_t}{k_t + k_r} {}_2F_1(1, \alpha, 1 + \alpha, -y), \quad (\text{B.6})$$

when the trapping energy distribution is exponential, Eq. (14).

Following the derivation of Eq. (17) from Eq. (15) we have from Eq. (B.5) for $y \gg 1$,

$$\rho \simeq \left(\frac{\pi \alpha}{\sin(\pi \alpha)} \frac{k_t}{k_t + k_r} \right)^{1/(\alpha+1)} \left(\frac{k_t + k_r}{2k_r} \frac{G}{N} \right)^{\alpha/(\alpha+1)}. \quad (\text{B.7})$$

Equation (B.7) shows that the number density of holes obeys essentially the same power law dependence on the light intensity as shown in Eq. (17). By introducing Eq. (B.7) into Eq. (B.4), the quasi-Fermi energy of a hole given by $\epsilon_F = \ln(y)$ is expressed as,

$$\epsilon_F = \frac{1}{\alpha + 1} \left[\ln \left(\frac{\pi\alpha}{\sin \pi\alpha} \right) + \ln \left(\frac{2k_t k_r}{(k_t + k_r)^2} \right) - \ln(G/N) \right]. \quad (\text{B.8})$$

While following the derivation of Eq. (27) from Eq. (11) we have from Eq. (B.5) for $y \gg 1$,

$$\rho \simeq \left(\frac{k_t + k_r}{k_t} + \frac{2k_r \hat{g}(1) N}{k_t + k_r} \frac{1}{G} \right)^{-1}. \quad (\text{B.9})$$

In this limit, the number density saturates as the generation rate, G , increases. The fraction ρ of trap sites occupied by carriers saturates when the light intensity is high. The saturation results from the trap filling of the deep trap levels inside the band gap up to the shallow trap levels. Note that Eq. (B.9) is derived without assuming any form of the trapping energy distribution. $\hat{g}(1) = \alpha/(1 + \alpha)$ is obtained for the exponential trapping energy distribution. By using Eq. (B.9), Eq. (B.4) can be expressed as,

$$\begin{aligned} y &\simeq \left[\hat{g}(1) + \frac{(k_t + k_r)^2}{2k_t k_r} \frac{1}{N} \right]^{-1} \\ &\simeq \frac{2k_t k_r}{(k_t + k_r)^2} \frac{1}{G}, \end{aligned} \quad (\text{B.10})$$

where Eq. (40) and $1 > \hat{g}(1)$ are used. As a result, $\epsilon_F = \ln y$ is obtained as,

$$\epsilon_F \simeq \ln \left(\frac{2k_t k_r}{(k_t + k_r)^2} \right) - \ln(G/N). \quad (\text{B.11})$$

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